

# NCV8411

## Self-Protected Low Side Driver with In-Rush Current Management

The NCV8411 is a three terminal protected Low-Side Smart Discrete FET. The protection features include Delta Thermal Shutdown, overcurrent, overtemperature, ESD and integrated Drain to Gate clamping for over voltage protection. The device also offers fault indication via the gate pin. This device is suitable for harsh automotive environments.

### Features

- Short Circuit Protection with In-Rush Current Management
- Delta Thermal Shutdown
- Thermal Shutdown with Automatic Restart
- Over Voltage Protection
- Integrated Clamp for Over Voltage Protection and Inductive Switching
- ESD Protection
- dV/dt Robustness
- Analog Drive Capability (Logic Level Input)
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

### Typical Applications

- Switch a Variety of Resistive, Inductive and Capacitive Loads
- Can Replace Electromechanical Relays and Discrete Circuits
- Automotive / Industrial

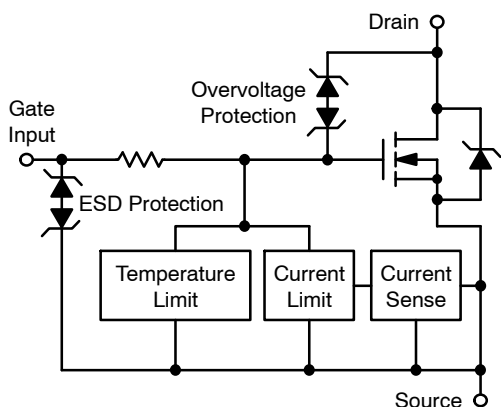


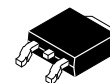
Figure 1. Block Diagram



ON Semiconductor®

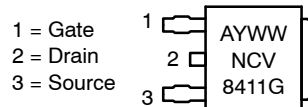
[www.onsemi.com](http://www.onsemi.com)

V <sub>DSS</sub> (Clamped)	R <sub>DS(ON)</sub> TYP	I <sub>D</sub> MAX (Limited)
42 V	23 mΩ @ 10 V	45 A



DPAK  
CASE 369C  
STYLE 2

### MARKING DIAGRAM



A = Assembly Location  
Y = Year  
WW = Work Week  
G = Pb-Free Package

### ORDERING INFORMATION

Device	Package	Shipping†
NCV8411DTRKG	DPAK (Pb-Free)	2500/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

**Table 1. MAXIMUM RATINGS**

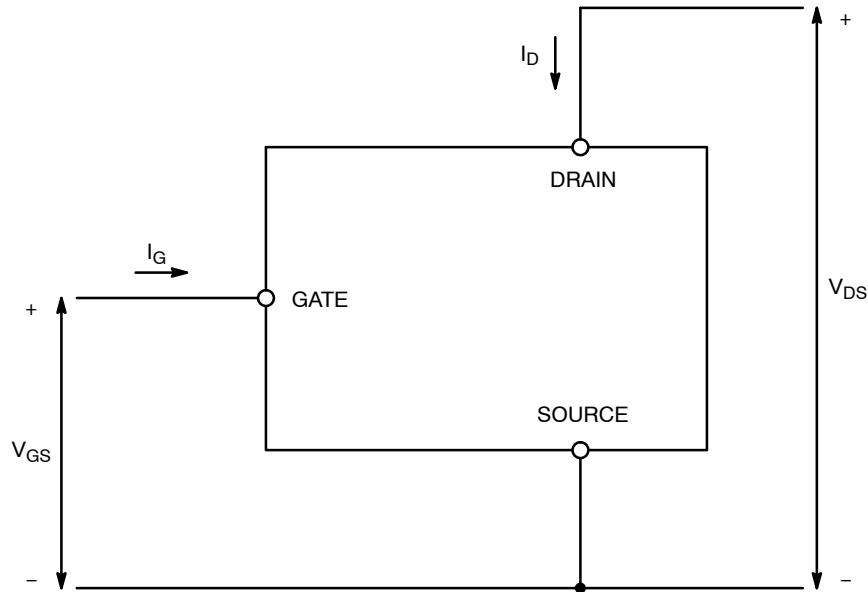
Rating	Symbol	Value (min)	Unit
Drain-to-Source Voltage Internally Clamped	$V_{DSS}$	42	V
Drain-to-Gate Voltage Internally Clamped	$V_{DG}$	42	V
Gate-to-Source Voltage	$V_{GS}$	$\pm 14$	V
Drain Current – Continuous	$I_D$	Internally Limited	
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ (Note 1) @ $T_A = 25^\circ\text{C}$ (Note 2)	$P_D$	1.3 2.7	W
Thermal Resistance Junction-to-Case Junction-to-Ambient (Note 1) Junction-to-Ambient (Note 2)	$R_{thJC}$ $R_{thJA}$ $R_{thJA}$	0.65 95 45	$^\circ\text{C/W}$
Single Pulse Inductive Load Switching Energy (Note 3) ( $L = 120\text{ mH}$ , $T_{J(start)} = 150^\circ\text{C}$ )	$E_{AS}$	600	mJ
Load Dump Voltage ( $V_{GS} = 0$ and $10\text{ V}$ , $R_G = 2\ \Omega$ , $R_L = 3\ \Omega$ ) (Note 4)	$U_S^*$	55	V
Operating Junction Temperature	$T_J$	-40 to 150	$^\circ\text{C}$
Storage Temperature	$T_{storage}$	-55 to 150	$^\circ\text{C}$

**ESD CHARACTERISTICS** (Note 3)

Electro-Static Discharge Capability Human Body Model (HBM)	ESD	4	kV
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Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Mounted onto a 2" square FR4 board (100 sq mm, 1 oz. Cu, steady state)
2. Mounted onto a 2" square FR4 board (645 sq mm, 1 oz. Cu, steady state)
3. Not tested in production.
4. Load Dump Test B (with centralized load dump suppression) according to ISO16750-2 standard. Guaranteed by design. Not tested in production. Passed Class C according to ISO16750-1.



**Figure 2. Voltage and Current Convention**

# NCV8411

**Table 2. ELECTRICAL CHARACTERISTICS** ( $T_J = 25^\circ\text{C}$  unless otherwise noted)

Characteristic	Test Conditions	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>						
Drain-to-Source Clamped Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	$V_{(BR)DSS}$	42	46	50	V
	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}, T_J = 150^\circ\text{C}$ (Note 5)		42	44	50	
Zero Gate Voltage Drain Current	$V_{DS} = 32\text{ V}, V_{GS} = 0\text{ V}$	$I_{DSS}$	-	1.5	5	$\mu\text{A}$
	$V_{DS} = 32\text{ V}, V_{GS} = 0\text{ V}, T_J = 150^\circ\text{C}$ (Note 5)		-	5.5	-	
Gate Input Current	$V_{GS} = 5\text{ V}, V_{DS} = 0\text{ V}$	$I_{GSS}$	-	50	100	$\mu\text{A}$

**ON CHARACTERISTICS**

Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 1.2\text{ mA}$	$V_{GS(th)}$	1.0	1.8	2.5	V
Threshold Temperature Coefficient	$V_{GS} = V_{DS}, I_D = 1.2\text{ mA}$ (Note 5)		-	5	-	$\text{mV}/^\circ\text{C}$
Static Drain-to-Source On Resistance	$V_{GS} = 10\text{ V}, I_D = 5\text{ A}, T_J = 25^\circ\text{C}$	$R_{DS(ON)}$	-	23	29	$\text{m}\Omega$
	$V_{GS} = 10\text{ V}, I_D = 5\text{ A}, T_J = 150^\circ\text{C}$ (Note 5)		-	43	55	
	$V_{GS} = 5\text{ V}, I_D = 5\text{ A}, T_J = 25^\circ\text{C}$		-	28	34	
	$V_{GS} = 5\text{ V}, I_D = 5\text{ A}, T_J = 150^\circ\text{C}$ (Note 5)		-	50	60	
Source Drain Forward On Voltage	$I_S = 5\text{ A}, V_{GS} = 0\text{ V}$	$V_{SD}$	-	0.8	1.1	V

**SWITCHING CHARACTERISTICS** (Note 5)

Turn-On Time (10% $V_{GS}$ to 90% $I_D$ )	$V_{GS} = 0\text{ V to } 5\text{ V}, V_{DS} = 12\text{ V}, I_D = 1\text{ A}$	$t_{ON}$	-	29	50	$\mu\text{s}$
Turn-Off Time (90% $V_{GS}$ to 10% $I_D$ )		$t_{OFF}$	-	53	150	
Turn-On Time (10% $V_{GS}$ to 90% $I_D$ )	$V_{GS} = 0\text{ V to } 10\text{ V}, V_{DS} = 12\text{ V}, I_D = 1\text{ A}$	$t_{ON}$	-	14	25	$\mu\text{s}$
Turn-Off Time (90% $V_{GS}$ to 10% $I_D$ )		$t_{OFF}$	-	80	180	
Slew Rate On (80% $V_{DS}$ to 50% $V_{DS}$ )	$V_{GS} = 0\text{ V to } 10\text{ V}, V_{DD} = 12\text{ V}, R_L = 4.7\ \Omega$	$-dV_{DS}/dt_{ON}$	-	1.52	2.5	$\text{V}/\mu\text{s}$
Slew Rate Off (50% $V_{DS}$ to 80% $V_{DS}$ )		$dV_{DS}/dt_{OFF}$	-	0.71	0.85	

**SELF PROTECTION CHARACTERISTICS**

Current Limit	$V_{GS} = 5\text{ V}, V_{DS} = 10\text{ V}$	$I_{LIM}$	29	33	40	A
	$V_{GS} = 5\text{ V}, V_{DS} = 10\text{ V}, T_J = 150^\circ\text{C}$ (Note 5)		27	31	37	
	$V_{GS} = 10\text{ V}, V_{DS} = 10\text{ V}$ (Note 5)		23	34	46	
	$V_{GS} = 10\text{ V}, V_{DS} = 10\text{ V}, T_J = 150^\circ\text{C}$ (Note 5)		23	33	46	
Temperature Limit (Turn-Off)	$V_{GS} = 5\text{ V}$ (Note 5)	$T_{LIM(OFF)}$	150	170	185	$^\circ\text{C}$
Thermal Hysteresis		$\Delta T_{LIM(ON)}$	-	10	-	
Temperature Limit (Turn-Off)	$V_{GS} = 10\text{ V}$ (Note 5)	$T_{LIM(OFF)}$	150	180	200	$^\circ\text{C}$
Thermal Hysteresis		$\Delta T_{LIM(ON)}$	-	10	-	

**GATE INPUT CHARACTERISTICS** (Note 5)

Device ON Gate Input Current – Normal Operation	$V_{GS} = 5\text{ V}, V_{DS} = 10\text{ V}, I_D = 1\text{ A}$	$I_{GON}$	-	50	100	$\mu\text{A}$
	$V_{GS} = 10\text{ V}, V_{DS} = 10\text{ V}, I_D = 1\text{ A}$		200	318	500	
Device ON Gate Input Current – Thermal Limit	$V_{GS} = 5\text{ V}, V_{DS} = 10\text{ V}, I_D = 0\text{ A}$	$I_{GTL}$	-	633	900	$\mu\text{A}$
	$V_{GS} = 10\text{ V}, V_{DS} = 10\text{ V}, I_D = 0\text{ A}$		-	1470	2000	
Device ON Gate Input Current – Current Limit	$V_{GS} = 5\text{ V}, V_{DS} = 10\text{ V}$	$I_{GCL}$	-	245	600	$\mu\text{A}$
	$V_{GS} = 10\text{ V}, V_{DS} = 10\text{ V}$		-	1121	1500	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Not tested in production.

TYPICAL PERFORMANCE CURVES

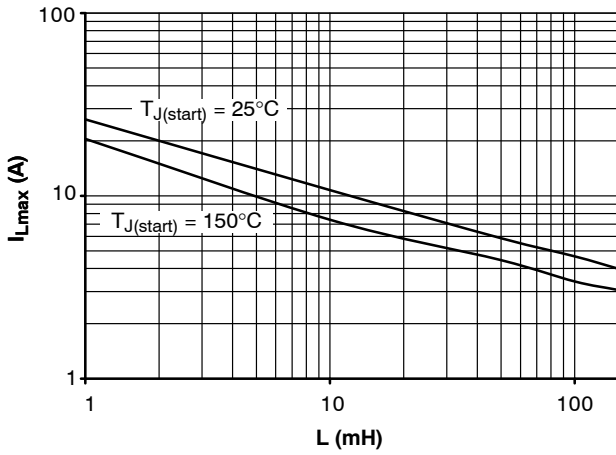


Figure 3. Single Pulse Maximum Switch-off Current vs. Load Inductance

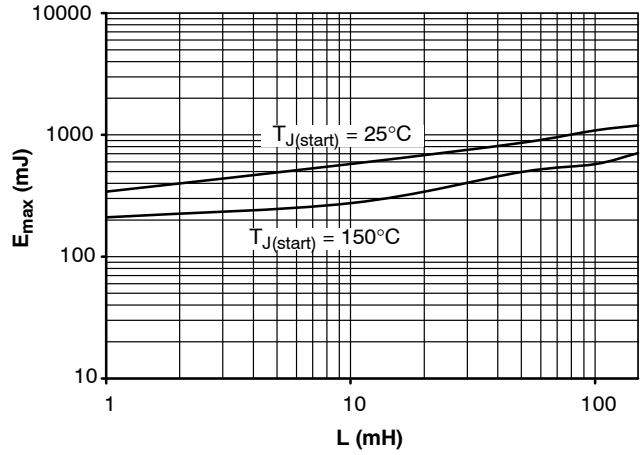


Figure 4. Single Pulse Maximum Switching Energy vs. Load Inductance

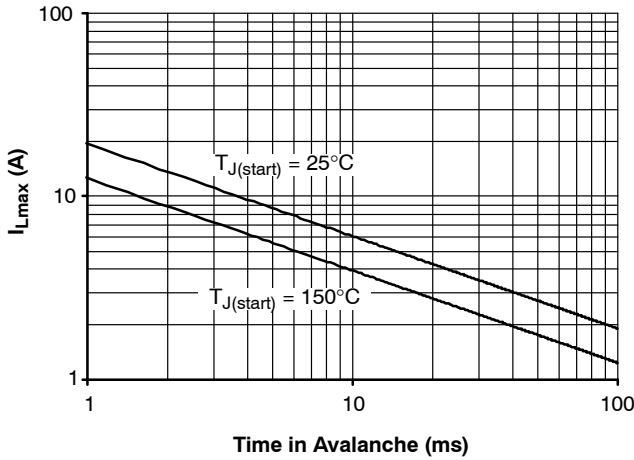


Figure 5. Single Pulse Maximum Inductive Switch-off Current vs. Time in Avalanche

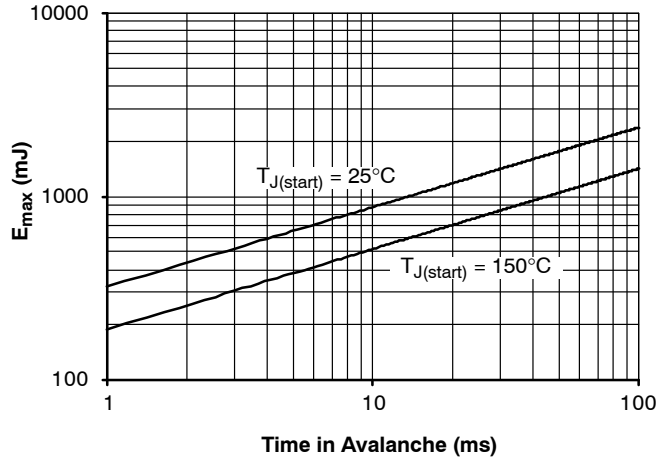


Figure 6. Single Pulse Maximum Inductive Switching Energy vs. Time in Avalanche

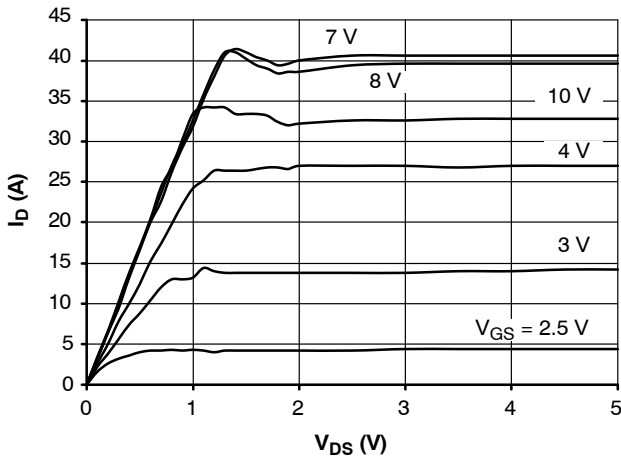


Figure 7. On-state Output Characteristics at 25°C

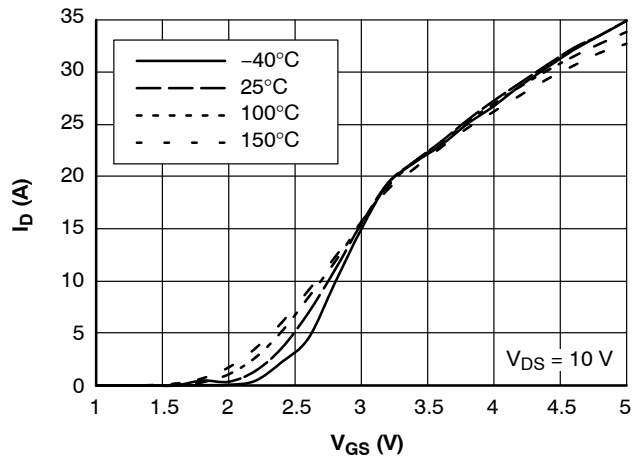


Figure 8. Transfer Characteristics

TYPICAL PERFORMANCE CURVES

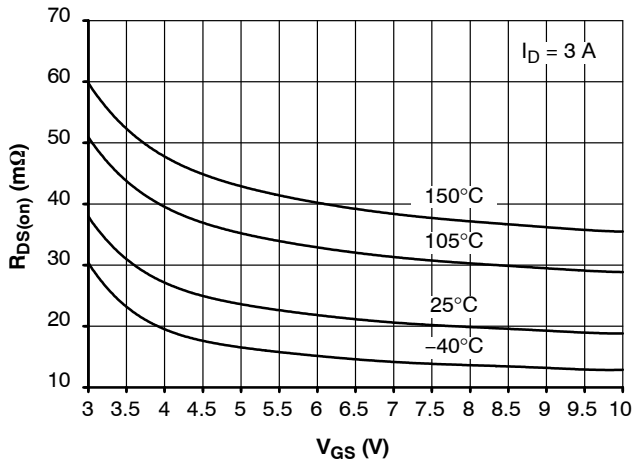


Figure 9.  $R_{DS(on)}$  vs. Gate-Source Voltage

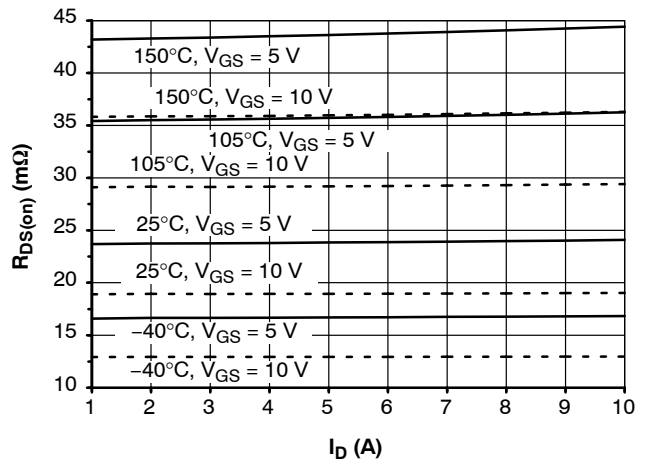


Figure 10.  $R_{DS(on)}$  vs. Drain Current

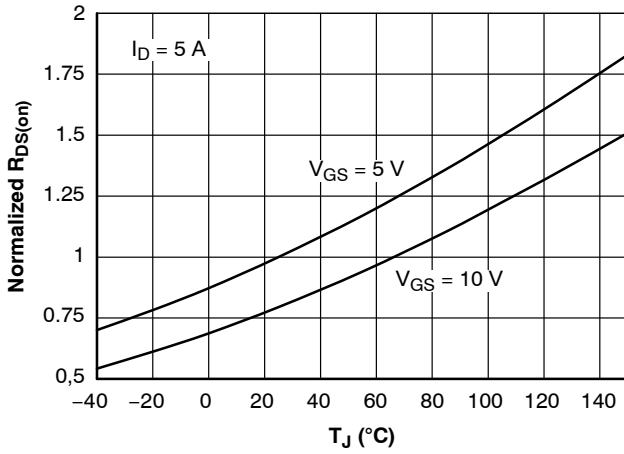


Figure 11. Normalized  $R_{DS(on)}$  vs. Temperature

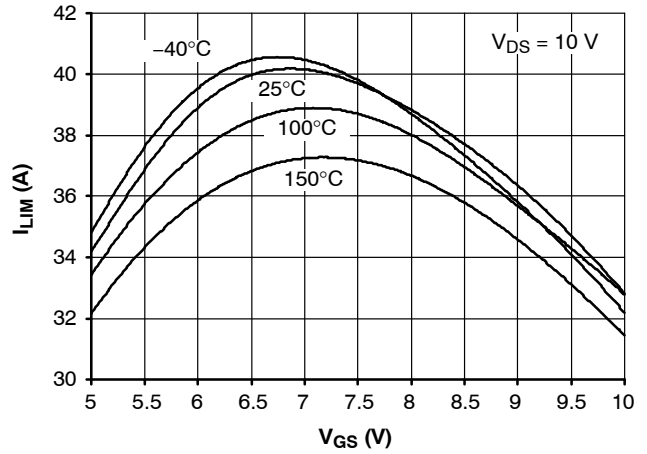


Figure 12. Current Limit vs. Gate-Source Voltage

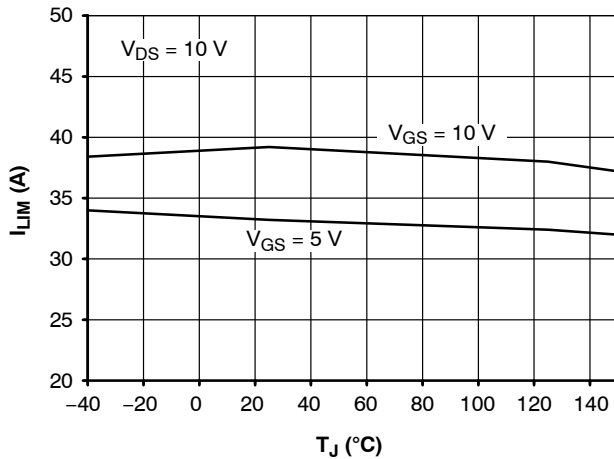


Figure 13. Current Limit vs. Junction Temperature

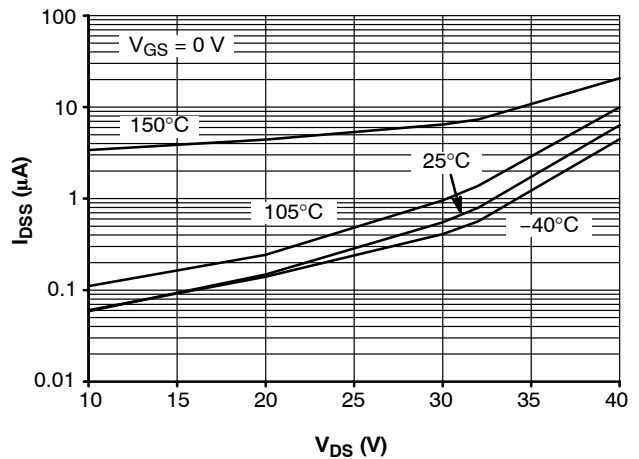


Figure 14. Drain-to-Source Leakage Current

TYPICAL PERFORMANCE CURVES

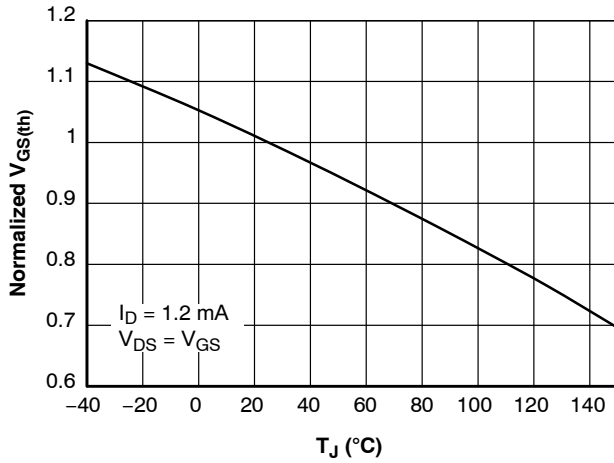


Figure 15. Normalized Threshold Voltage vs. Temperature

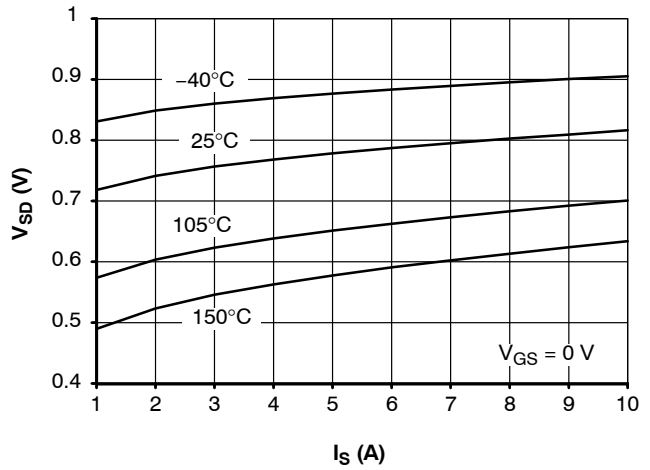


Figure 16. Source-Drain Diode Forward Characteristics

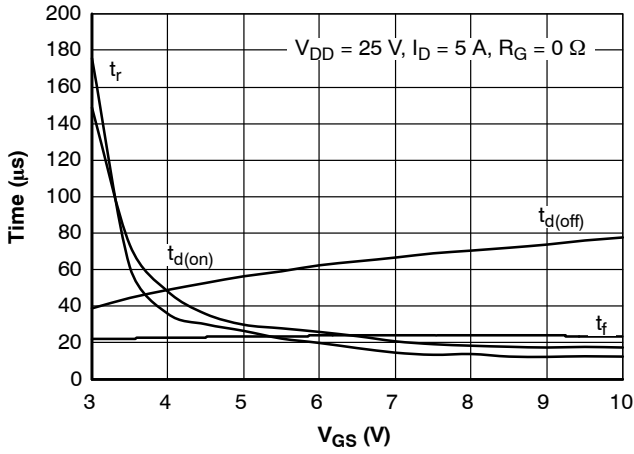


Figure 17. Resistive Load Switching Time vs. Gate-Source Voltage

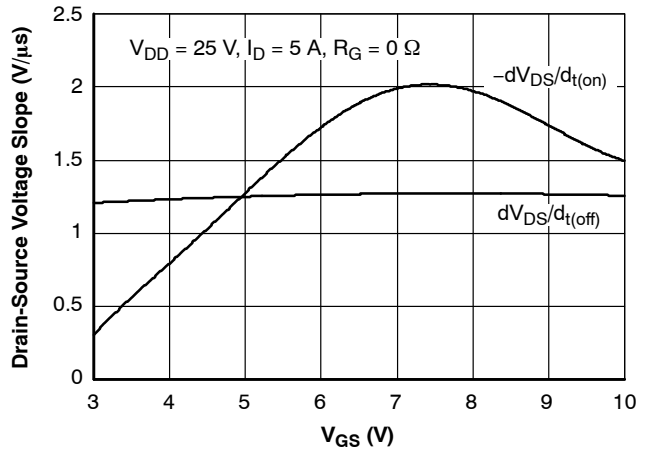


Figure 18. Resistive Load Switching Drain-Source Voltage Slope vs. Gate-Source Voltage

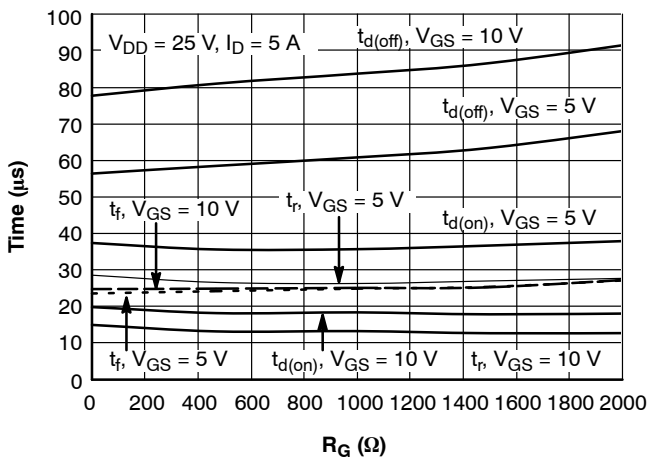


Figure 19. Resistive Load Switching Time vs. Gate Resistance

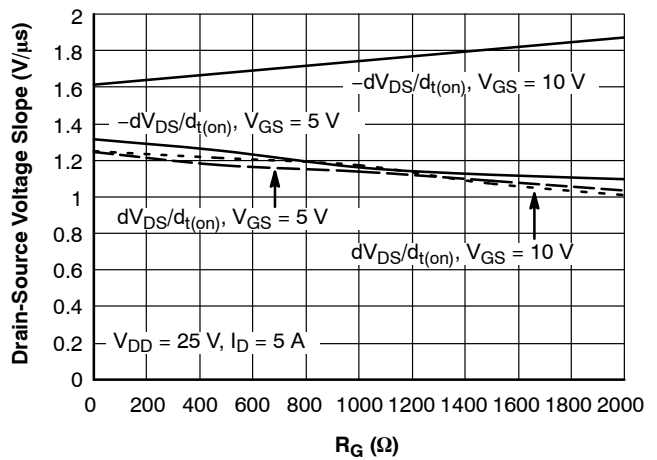


Figure 20. Drain-Source Voltage Slope during Turn On and Turn Off vs. Gate Resistance

# NCV8411

## TYPICAL PERFORMANCE CURVES

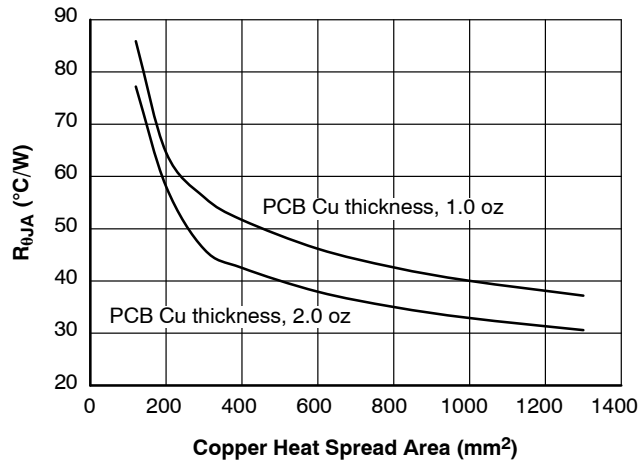


Figure 21. R<sub>θJA</sub> vs. Copper Area

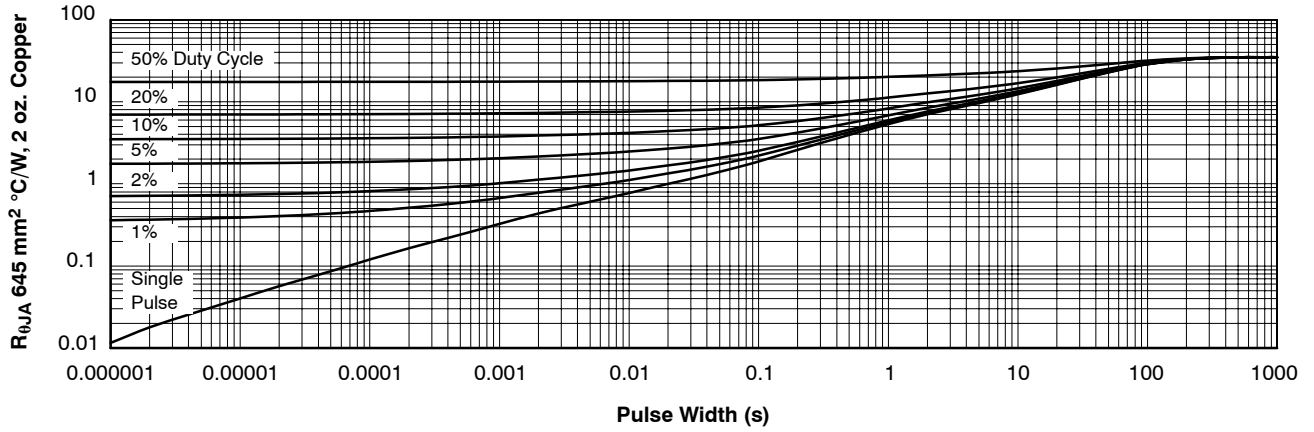


Figure 22. Transient Thermal Resistance

APPLICATION INFORMATION

**Circuit Protection Features**

The NCV8411 has three main protections. Current Limit, Thermal Shutdown and Delta Thermal Shutdown. These protections establish robustness of the NCV8411.

**Current Limit and Short Circuit Protection**

The NCV8411 has current sense element. In the event that the drain current reaches designed current limit level, integrated Current Limit protection establishes its constant level.

**Delta Thermal Shutdown**

Delta Thermal Shutdown (DTSD) Protection increases higher reliability of the NCV8411. DTSD consist of two independent temperature sensors – cold and hot sensors. The

NCV8411 establishes a slow junction temperature rise by sensing the difference between the hot and cold sensors. ON/OFF output cycling is designed with hysteresis that results in a controlled saw tooth temperature profile (Figure 23). The die temperature slowly rises (DTSD) until the absolute temperature shutdown (TSD) is reached around 175°C.

**Thermal Shutdown with Automatic Restart**

Internal Thermal Shutdown (TSD) circuitry is provided to protect the NCV8411 in the event that the maximum junction temperature is exceeded. When activated at typically 175°C, the NCV8411 turns off. This feature is provided to prevent failures from accidental overheating.

TEST CIRCUITS AND WAVEFORMS

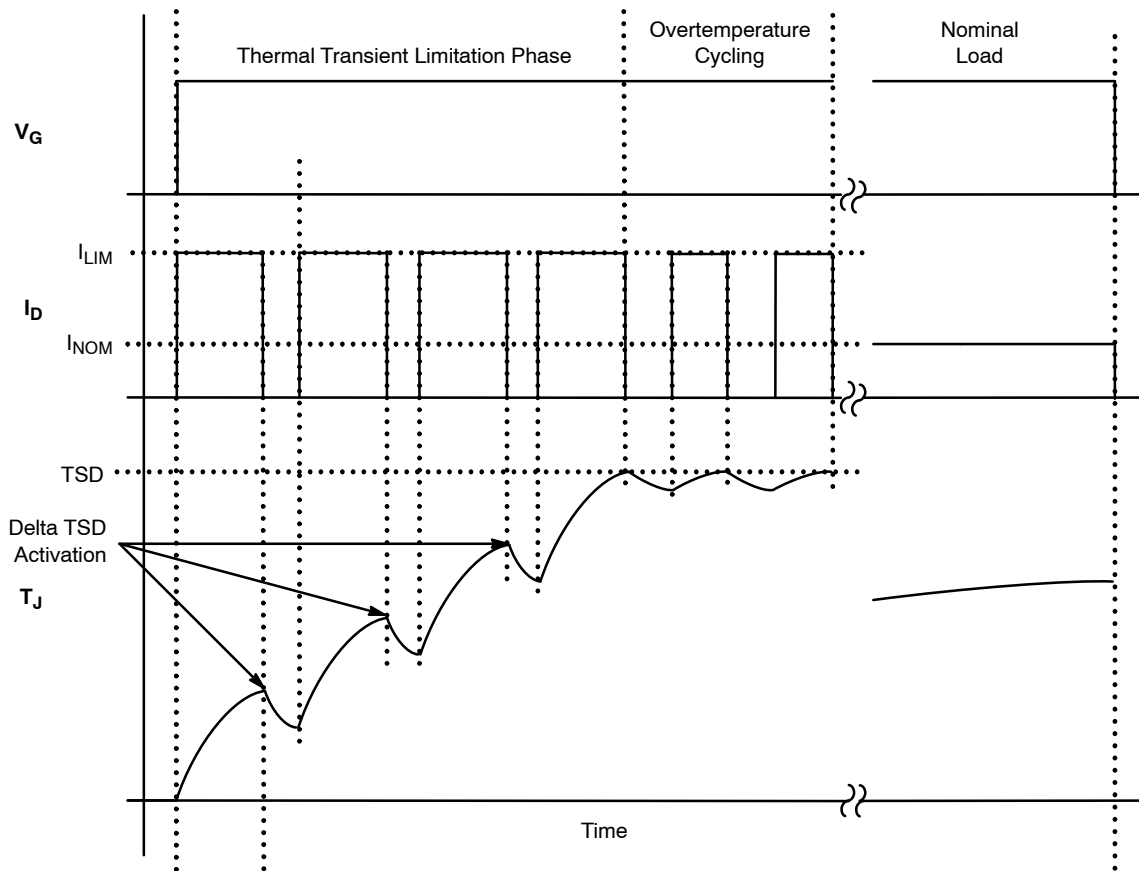


Figure 23. Overload Protection Behavior



TEST CIRCUITS AND WAVEFORMS

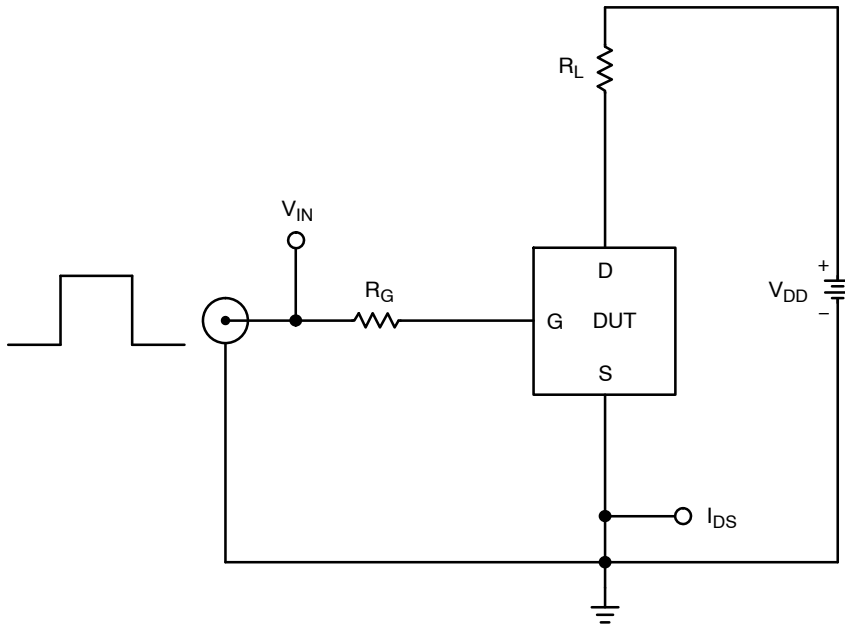


Figure 24. Resistive Load Switching Test Circuit

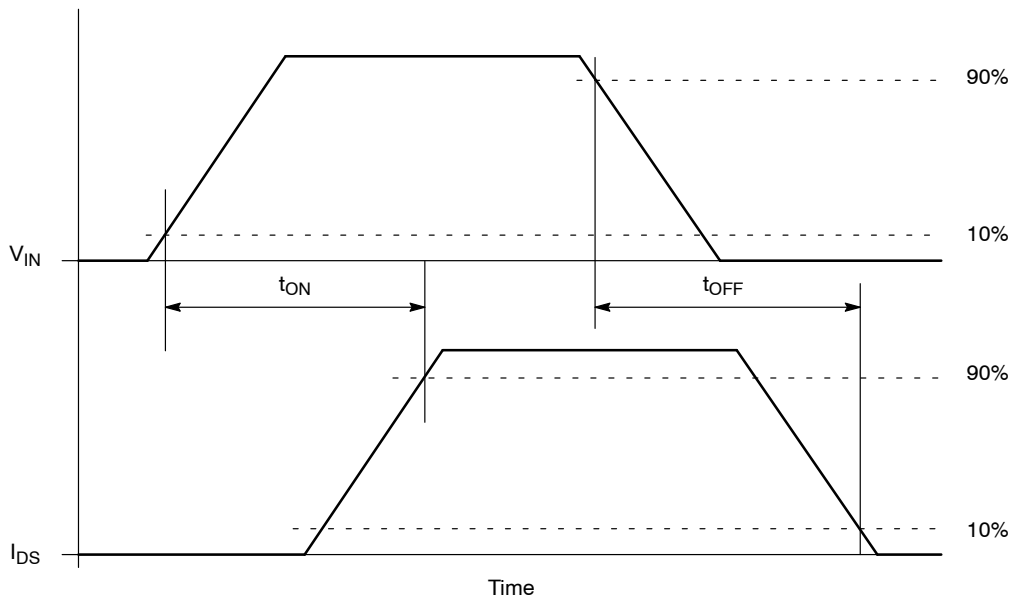


Figure 25. Resistive Load Switching Waveforms

# NCV8411

## TEST CIRCUITS AND WAVEFORMS

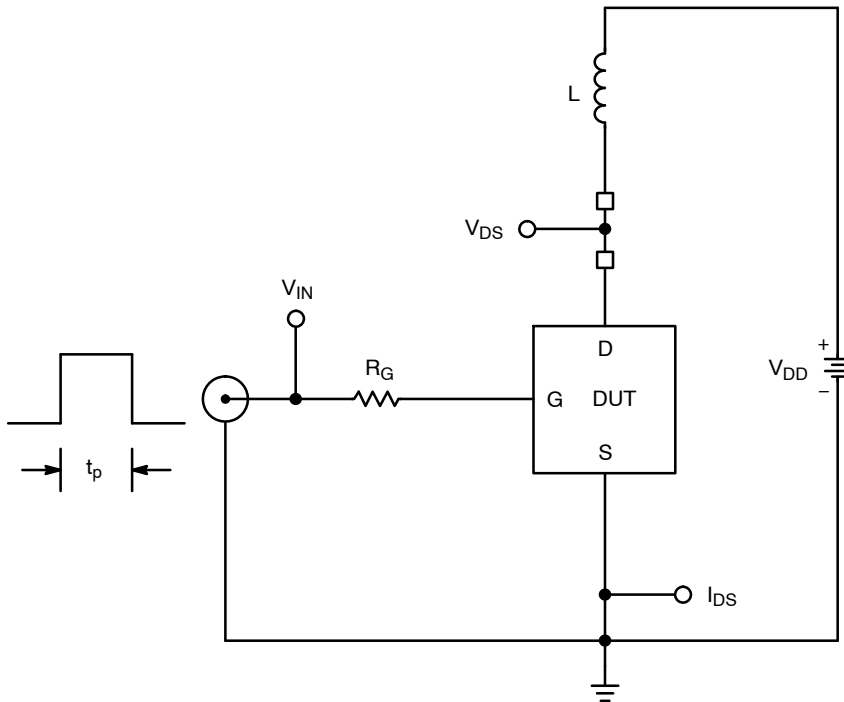


Figure 26. Inductive Load Switching Test Circuit

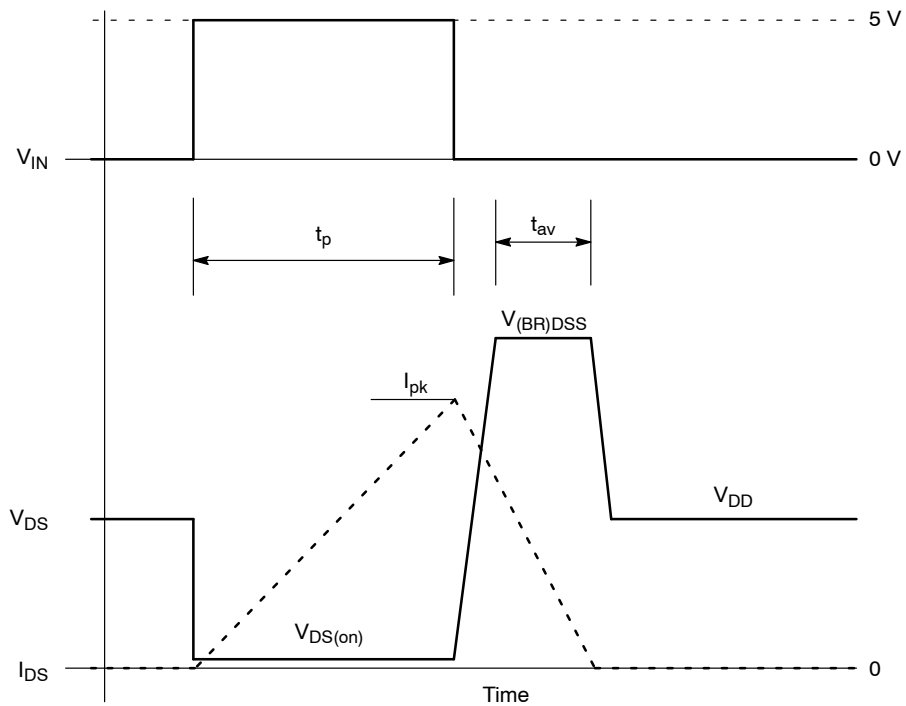
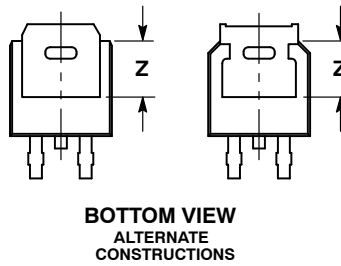
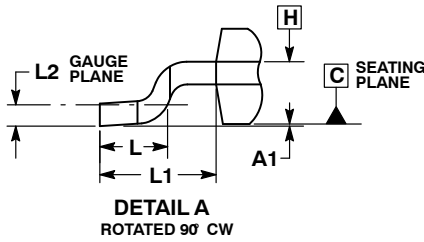
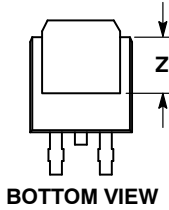
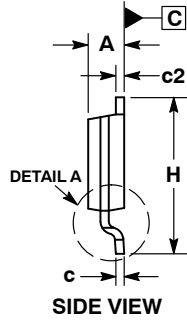
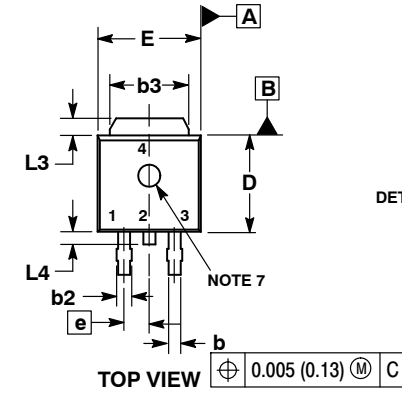


Figure 27. Inductive Load Switching Waveform

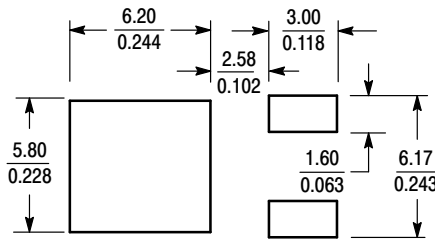
# NCV8411

## PACKAGE DIMENSIONS

### DPAK CASE 369C ISSUE F



### SOLDERING FOOTPRINT\*



SCALE 3:1  $\left(\frac{\text{mm}}{\text{inches}}\right)$

#### NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
7. OPTIONAL MOLD FEATURE.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090	BSC	2.29	BSC
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114	REF	2.90	REF
L2	0.020	BSC	0.51	BSC
L3	0.035	0.050	0.89	1.27
L4	---	0.040	---	1.01
Z	0.155	---	3.93	---

#### STYLE 2:

- PIN 1. GATE
- DRAIN
- SOURCE
- DRAIN

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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